

Application No.: 10/065,761

Docket No.: JCLA8016

**AMENDMENTS****In the Claims:**

1. (currently amended) A programming method of the multi-level flash memory, comprising:  
~~applying shooting~~ a programming voltage ~~that is increasing upwards stepwise each time into~~  
~~a gate of the multi-level flash memory~~ to change a state of the multi-level flash memory; and  
~~applying shooting~~ an additional programming voltage into the multi-level flash memory  
after the last programming voltage is ~~shot~~ applied when a highest value of the multi-level is  
being programmed in the multi-level flash memory, wherein the additional programming voltage  
is capable of adjusting the state of the highest value of the multi-level flash memory.
2. (original) The method of claim 1, wherein the programming method can be used in a  
binary flash memory.
3. (currently amended) A programming method of the multi-level flash memory, comprising:  
~~applying shooting~~ a programming voltage ~~that is increasing upward stepwise each time into~~  
~~a gate of the multi-level flash memory~~ to change ~~a state~~ state of the multi-level flash memory; and  
~~applying shooting~~ an additional programming voltage into the multi-level flash memory  
after the last programming voltage is applied ~~shot~~ when a value of the multi-level is being  
programmed in the multi-level flash memory, wherein the additional programming voltage is  
capable of adjusting the state of the value of the multi-level flash memory.
4. (original) The method of claim 3, wherein the programming method can be used in a  
binary flash memory.

**Claim 5 (canceled)**